PAS 5500/100D

i-Line Stepper

Description

The PAS 5500/100D i-line stepper is designed for mass production at 0.4 µm and achieves extremely high throughput while maintaining the utmost versatility with its variable Numerical Aperture (NA). This stepper extends i-line's capability for manufacturing multiple generations of sub-half-micron design rules by optimizing both depth of focus and resolution for critical process layers.

Technical Specifications

Lens	
Wavelength:	365 nm
NA:	0.48—0.60 (variable)
Resolution:	0.40 μm
Field size, for reticle with pellicle	
• Diameter:	31.1 mm
• Max X:	22.0 mm
• Max Y:	27.4 mm
Usable depth of focus:	≥ 1.1 µm
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Distortion:	≤ 60 nm
Overlay	
99.7% with 2 pt. Global Alignment:	< 60 nm
Production Throughput	
With field-by-field leveling, 200-mJ/cm ² dose and at specified overlay accuracy	
• 150-mm wafers, 40 shots:	≥ 100 wph
• 200-mm wafers, 70 shots:	≥ 72 wph
Illumination	
Intensity:	≥ 900 mW/cm ²
Uniformity:	≤ 1.5%
Variable coherence range:	$\sigma = 0.3$ —0.7

Key Features and Benefits

Automated Variable-NA i-Line Projection Lens Lens technology allowing 0.40-µm imaging.

Completely redesigned variable partial Coherence Illuminator

1.5-kW illuminator power results in 900 mW/cm² at wafer level.

Broadband Field-by-field Focus Leveling System Leveling while moving from one site to another.

Advanced Light-weight Stage
High precision combined with high throughput.

Direct Reticle-Referenced, Through-The-Lens (TTL)
Phase-Grating Alignment.
Optimum overlay and matching.

Built-In CLASS 1 Laminar Airflow

Enhances interferometer stability, provides ultra-clean wafer environment.

